R-C Thermal Model Parameters

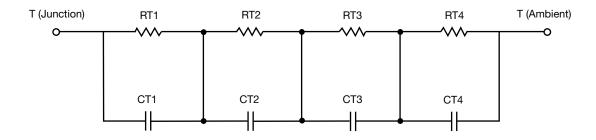
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DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	10.7586	328.6903m	N/A		
RT2	56.0523	1.2651	N/A		
RT3	5.6688	524.6707m	N/A		
RT4	12.3041	975.3874m	N/A		
	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	6.7715m	60.1655m	N/A		
CT2	1.3521	8.7319m	N/A		
CT3	115.1949m	1.4783m	N/A		
CT4	286.7213m	12.3685m	N/A		

Note

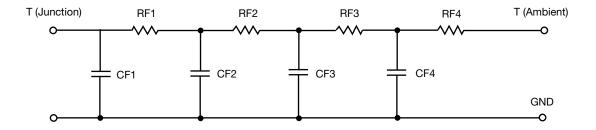
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	5.1243	760.1672m	N/A			
RF2	13.6789	1.5164	N/A			
RF3	22.8949	804.4327m	N/A			
RF4	43.1966	12.2001m	N/A			
	THERMAL CAPAC	TANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	2.2339m	1.0110m	N/A			
CF2	17.0410m	3.5217m	N/A			
CF3	350.5590m	4.7781m	N/A			
CF4	1.4793	31.1527u	N/A			

Note

• n/a indicates not applicable





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100ms

1.0s

Time: 20:23:05

Temperature: 27.0

